



HIGH POWER NPN TRANSISTOR

- STMicroelectronics PREFERRED SALESTYPE
- NPN TRANSISTOR
- HIGH CURRENT CAPABILITY
- FAST SWITCHING SPEED
- VERY LOW SATURATION VOLTAGE AND HIGH GAIN

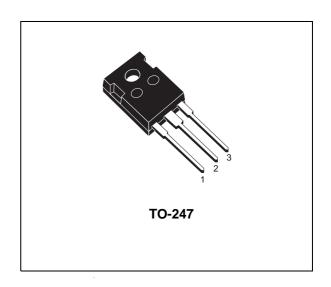
APPLICATION

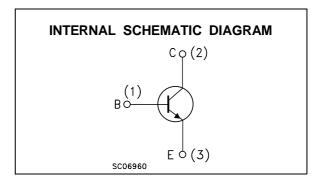
- SWITCHING REGULATORS
- MOTOR CONTROL
- HIGH FREQUENCY AND EFFICENCY CONVERTERS



The BUT70W is a Multiepitaxial planar NPN transistor in TO-247 plastic package.

It's intented for use in high frequency and efficiency converters such us motor controllers and industrial equipment.





ABSOLUTE MAXIMUM RATINGS

Symbol	Parameter	Value	Unit
V _{CEV}	Collector-emitter Voltage (V _{BE} = -1.5V)	200	V
V_{CEO}	Collector-emitter Voltage (I _B = 0)	125	V
V_{EBO}	Emitter-Base Voltage (I _C = 0)	7	V
I _{E(RMS)}	Emitter Current	40	Α
I _{EM}	Emitter Peak Current	120	Α
I_B	Base Current	8	Α
I_{BM}	Base Peak Current	24	Α
P_{tot}	Total Power Dissipation at T _{case} < 25 °C	200	W
T _{stg}	Storage Temperature	-65 to 150	°C
Tj	Max Operating Junction Temperature	150	°C

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THERMAL DATA

R _{thj-case} Therma	Resistance Junction-case	Max	0.63	°C/W	
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ELECTRICAL CHARACTERISTICS ($T_{case} = 25$ ^{o}C unless otherwise specified)

Symbol	Parameter	Test Conditions	Min.	Тур.	Max.	Unit
I _{CER}	Collector Cut-off Current ($R_{BE} = 5\Omega$)	V _{CE} = 200 V V _{CE} = 200 V T _C = 100°C			1 5	mA mA
I _{CEV}	Collector Cut-off Current (V _{BE} = -1.5V)	V _{CE} = 200 V V _{CE} = 200 V T _C = 100°C			1 4	mA mA
I _{EBO}	Emitter Cut-off Current (I _C = 0)	V _{EB} = 5 V			1	mA
V _{CEO(sus)} *	Collector-Emitter Sustaining Voltage (I _B = 0)	I _C = 0.2 A L = 25 mH	125			V
V _{(BR)EBO}	Emitter-Base Breakdown Voltage (I _C = 0)	I _E = 50 mA	7			V
V _{CE(sat)} *	Collector-Emitter Saturation Voltage	$\begin{split} I_C &= 70 \text{ A} & I_B = 7 \text{ A} \\ I_C &= 70 \text{ A} & I_B = 7 \text{ A} & T_C = 100^{\circ}\text{C} \\ I_C &= 35 \text{ A} & I_B = 1.75 \text{ A} \\ I_C &= 35 \text{ A} & I_B = 1.75 \text{ A} & T_C = 100^{\circ}\text{C} \end{split}$			0.9 1.5 0.9 1.2	V V V
V _{BE(sat)} *	Base-Emitter Saturation Voltage	$\begin{split} I_C &= 70 \text{ A} & I_B = 7 \text{ A} \\ I_C &= 70 \text{ A} & I_B = 7 \text{ A} & T_C = 100^{\circ}\text{C} \\ I_C &= 35 \text{ A} & I_B = 1.75 \text{ A} \\ I_C &= 35 \text{ A} & I_B = 1.75 \text{ A} & T_C = 100^{\circ}\text{C} \end{split}$			1.8 1.9 1.4 1.4	V V V
di _c /d _t *	Rated of Rise of on-state Collector Current	$V_{CC} = 100 \text{ V}$ $R_C = 0$ $I_{B1} = 3.5 \text{ A}$ $t_p = 3 \mu\text{s}$ $T_C = 100^{\circ}\text{C}$	140			A/μs

^{*} Pulsed: Pulse duration = 300 μs, duty cycle < 2 %

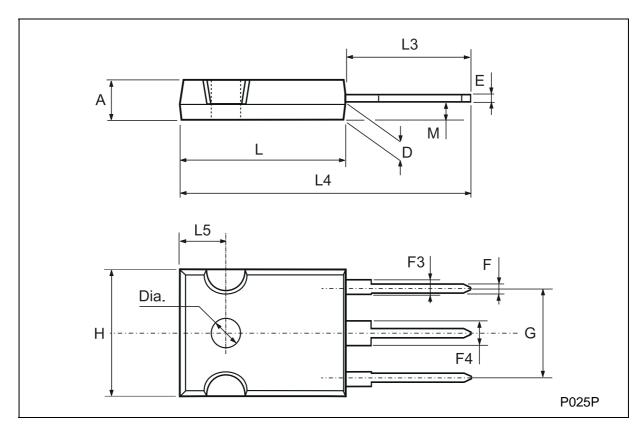
INDUCTIVE LOAD

Symbol	Parameter	Test Conditions		Min.	Тур.	Max.	Unit
ts	Storage Time	I _C = 35 A	$V_{CC} = 90 \text{ V}$			1.8	μs
t _f	Fall Time	$V_{BB} = -5 V$	$R_{B2} = 1.4 \Omega$			0.2	μs
tc		$I_{B1} = 1.75 A$ $V_{CLAMP} = 125V$	$L_C = 0.15 \text{ mH}$ $T_C = 100^{\circ}\text{C}$			0.35	μs

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TO-247 MECHANICAL DATA

DIM.	mm			inch			
	MIN.	TYP.	MAX.	MIN.	TYP.	MAX.	
Α	4.7		5.3	0.185		0.209	
D	2.2		2.6	0.087		0.102	
Е	0.4		0.8	0.016		0.031	
F	1		1.4	0.039		0.055	
F3	2		2.4	0.079		0.094	
F4	3		3.4	0.118		0.134	
G		10.9			0.429		
Н	15.3		15.9	0.602		0.626	
L	19.7		20.3	0.776		0.779	
L3	14.2		14.8	0.559		0.582	
L4		34.6			1.362		
L5		5.5			0.217		
М	2		3	0.079		0.118	



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